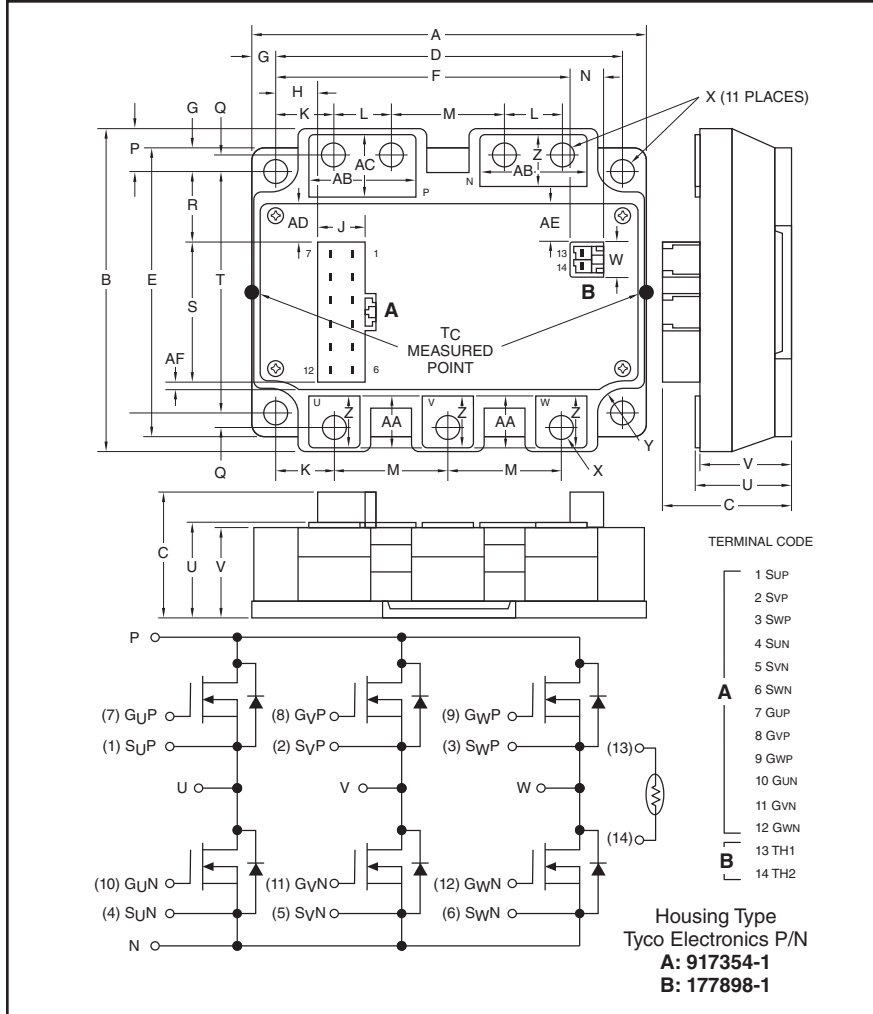


### 6-Pack High Power MOSFET Module 100 Amperes/150 Volts



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	4.33	110.0
B	3.54	90.0
C	1.38	35.0
D	3.82	97.0
E	3.15	80.0
F	3.27	83.0
G	0.26	6.5
H	0.48	12.0
J	0.51	12.9
K	0.65	16.5
L	0.63	16.0
M	1.26	32.0
N	0.35	8.8
P	0.45	11.5
Q	0.16	4.0

Dimensions	Inches	Millimeters
R	0.79	20.0
S	1.50	38.0
T	2.64	67.0
U	1.02	26.0
V	0.98	25.0
W	0.36	9.1
X	Dia. 0.25	Dia. 6.5
Y	Rad. 0.25	Rad. 6.5
Z	0.57	14.5
AA	0.55	14.0
AB	1.18	30.0
AC	0.69	17.5
AD	0.47	12.0
AE	0.61	15.5
AF	0.18	4.5



#### Description:

Powerex MOSFET Modules are designed for use in low voltage switching applications. Each module consists of 6 MOSFET switches with low  $R_{DS(on)}$  and a fast recovery body diode to yield low loss. All components and interconnects are isolated from the heat sink baseplate. This offers simplified system assembly and thermal management.

#### Features:

- Low  $E_{SW(off)}$  and Low  $R_{DS(on)}$
- Super-Fast Recovery Free-Wheel Diode
- Thermistor for  $T_C$  Sensing
- Parallel Legs to make a Dual Module at 3X the Rating
- Positive Locking Connectors
- Easy Bus Bar Layout Due to Flow Through Power Design

#### Applications:

- Forklift
- Off road Electric Vehicle
- Welder
- UPS
- Chopper

#### Ordering Information:

Example: Select the complete part module number you desire from the table below -i.e. FM200TU-3A is a 150V ( $V_{DSS}$ ), 100 Ampere 6-Pack High Power MOSFET Module.

Type	Current Rating Amperes	$V_{DSS}$ Volts
FM	100	150

## FM200TU-3A

### 6-Pack High Power MOSFET Module

100 Amperes/150 Volts

### Absolute Maximum Ratings, $T_j = 25^\circ\text{C}$ unless otherwise specified

Ratings	Symbol	FM200TU-07A	Units
Channel Temperature	$T_j$	-40 to 150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-40 to 125	$^\circ\text{C}$
Drain-Source Voltage (G-S Short)	$V_{DSS}$	150	Volts
Gate-Source Voltage (D-E Short)	$V_{GSS}$	$\pm 20$	Volts
Drain Current ( $T_C = 25^\circ\text{C}$ )	$I_{D(rms)}$	100	$A_{rms}$
Peak Drain Current (Pulse)	$I_{DM}$	200*	Amperes
Avalanche Current (L = 10 $\mu\text{H}$ , Pulse)	$I_{DA}$	100*	Amperes
Source Current ( $T_C = 25^\circ\text{C}$ )**	$I_{S(rms)}$	100	$A_{rms}$
Peak Source Current (Pulse)**	$I_{SM}$	200*	Amperes
Maximum Power Dissipation ( $T_C = 25^\circ\text{C}$ , $T_j < 150^\circ\text{C}$ )***	$P_D$	410	Watts
Maximum Peak Power Dissipation ( $T_C = 25^\circ\text{C}$ , $T_j < 150^\circ\text{C}$ )***	$P_D$	560	Watts
Mounting Torque, M6 Main Terminal	—	40	in-lb
Mounting Torque, M6 Mounting	—	40	in-lb
Weight	—	600	Grams
Isolation Voltage (Main Terminal to Baseplate, AC 1 min.)	$V_{ISO}$	2500	Volts

### Electrical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-Cutoff Current	$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0\text{V}$	—	—	1.0	mA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$I_D = 10\text{mA}$ , $V_{DS} = 10\text{V}$	4.7	6.0	7.3	Volts
Gate Leakage Current	$I_{GSS}$	$V_{GS} = V_{GSS}$ , $V_{DS} = 0\text{V}$	—	—	1.5	$\mu\text{A}$
Static Drain-Source On-State Resistance (Chip)	$r_{DS(on)}$	$I_D = 100\text{A}$ , $V_{GS} = 15\text{V}$ , $T_j = 25^\circ\text{C}$	—	4.8	6.6	$\text{m}\Omega$
		$I_D = 100\text{A}$ , $V_{GS} = 15\text{V}$ , $T_j = 125^\circ\text{C}$	—	9.1	—	$\text{m}\Omega$
Static Drain-Source On-State Voltage (Chip)	$V_{DS(on)}$	$I_D = 100\text{A}$ , $V_{GS} = 15\text{V}$ , $T_j = 25^\circ\text{C}$	—	0.48	0.66	Volts
		$I_D = 100\text{A}$ , $V_{GS} = 15\text{V}$ , $T_j = 125^\circ\text{C}$	—	0.91	—	Volts
Lead Resistance	$R_{lead}$	$I_D = 100\text{A}$ , Terminal-Chip, $T_j = 25^\circ\text{C}$	—	1.2	—	$\text{m}\Omega$
		$I_D = 100\text{A}$ , Terminal-Chip, $T_j = 125^\circ\text{C}$	—	1.68	—	$\text{m}\Omega$
Input Capacitance	$C_{iss}$		—	—	50	nf
Output Capacitance	$C_{oss}$	$V_{DS} = 10\text{V}$ , $V_{GS} = 0\text{V}$	—	—	7	nf
Reverse Transfer Capacitance	$C_{rss}$		—	—	4	nf
Total Gate Charge	$Q_G$	$V_{DD} = 80\text{V}$ , $I_D = 100\text{A}$ , $V_{GS} = 15\text{V}$	—	820	—	nC
Inductive Load	Turn-on Delay Time	$t_{d(on)}$	—	—	400	ns
	Rise Time	$t_r$	—	—	250	ns
Switching Time	Turn-off Delay Time	$t_{d(off)}$	—	—	450	ns
	Fall Time	$t_f$	—	—	200	ns
Diode Reverse Recovery Time**	$t_{rr}$	$I_S = 100\text{A}$	—	—	200	ns
Diode Reverse Recovery Charge**	$Q_{rr}$		—	6.5	—	$\mu\text{C}$
Source-Drain Voltage	$V_{SD}$	$I_S = 100\text{A}$ , $V_{GS} = 0\text{V}$	—	—	1.3	Volts

\* Pulse width and repetition rate should be such that device channel temperature ( $T_j$ ) does not exceed  $T_{j(max)}$  rating.

\*\*Represents characteristics of the anti-parallel, source-to-drain free-wheel diode (FWDi).

\*\*\* $T_C$ : measured point is just under the chips. If you use this value,  $R_{th(f-a)}$  should be measured just under the chips.

**FM200TU-3A**  
**6-Pack High Power MOSFET Module**  
 100 Amperes/150 Volts

**Thermal and Mechanical Characteristics,  $T_j = 25^\circ\text{C}$  unless otherwise specified**

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Channel to Case	$R_{th(j-c)}$	MOSFET part (1/6 Module) $T_C$ Reference Point per Outline Drawing	—	—	0.30	$^\circ\text{C/W}$
Thermal Resistance, Channel to Case	$R_{th(j-c')}$	MOSFET part (1/6 Module) Measured Point is Just Under the Chips.	—	—	0.22	$^\circ\text{C/W}$
Contact Thermal Resistance	$R_{th(c-f)}$	Per 1/6 Module, Thermal Grease Applied	—	0.1	—	$^\circ\text{C/W}$

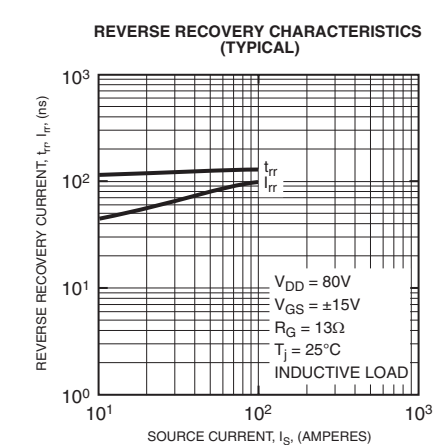
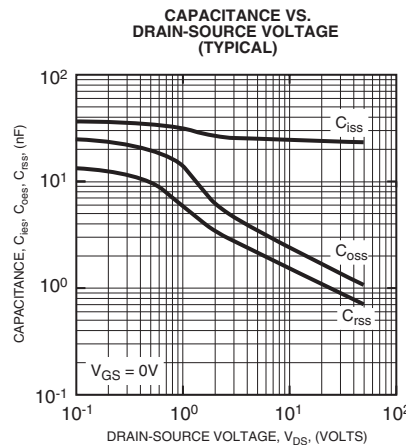
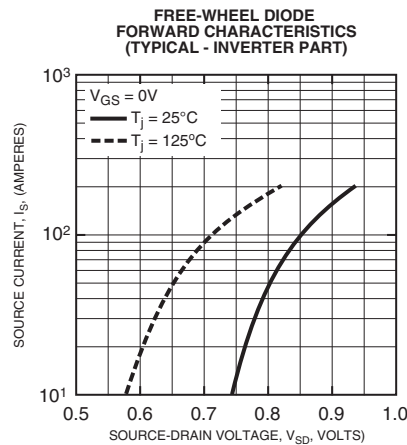
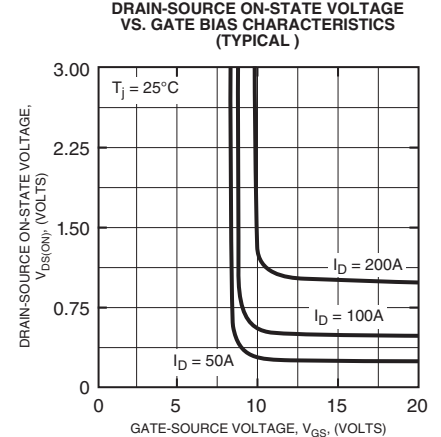
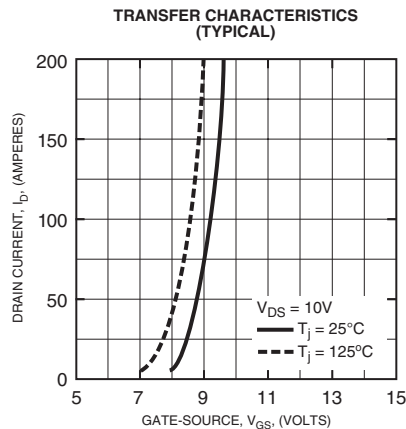
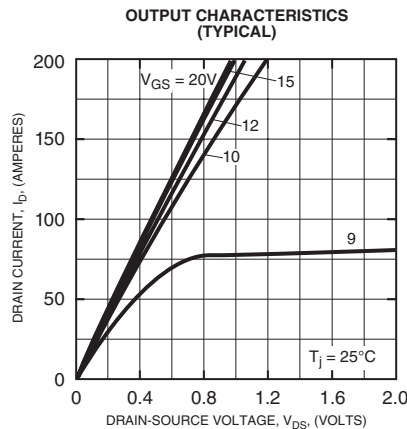
**Thermistors Part**

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Resistance*	$R_{th}$	$T_C = 25^\circ\text{C}$	—	100	—	$\text{k}\Omega$
B Constant*	B	Resistance at $25^\circ\text{C}$ , $50^\circ\text{C}$	—	4000	—	K

\* $B = (\ln R_1 - \ln R_2) / (1/T_1 - 1/T_2)$

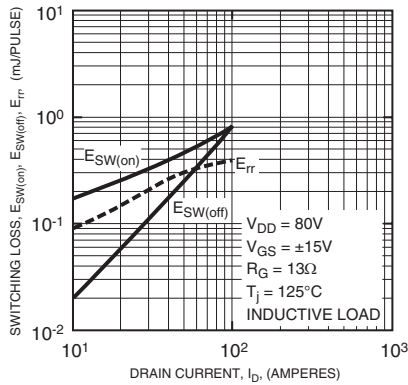
$R_1$ : Resistance at  $T_1$ (K),

$R_2$ : Resistance at  $T_2$ (K)

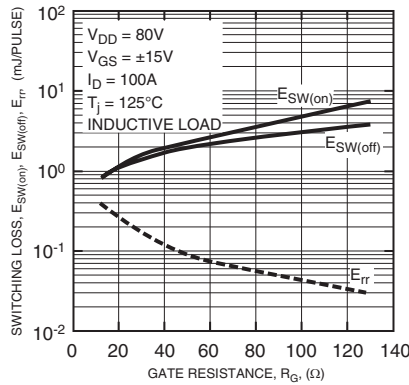


**FM200TU-3A**  
**6-Pack High Power MOSFET Module**  
 100 Amperes/150 Volts

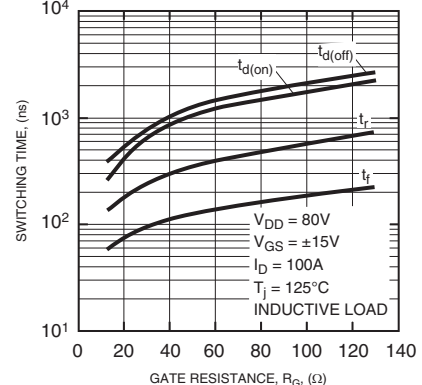
**SWITCHING LOSS VS. DRAIN CURRENT (TYPICAL)**



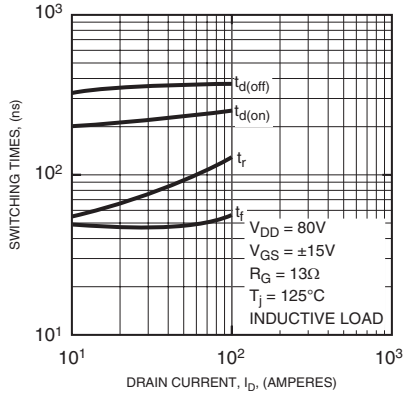
**SWITCHING LOSS VS. GATE RESISTANCE (TYPICAL)**



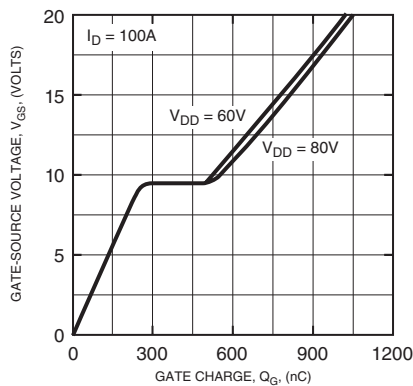
**SWITCHING TIME VS. GATE RESISTANCE (TYPICAL)**



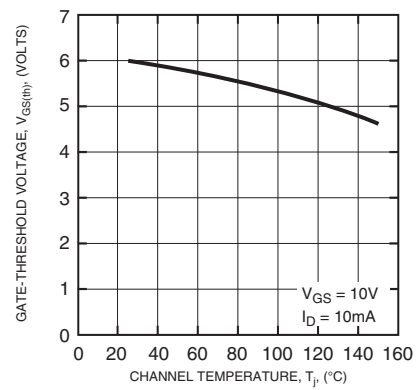
**SWITCHING TIME VS. DRAIN CURRENT (TYPICAL)**



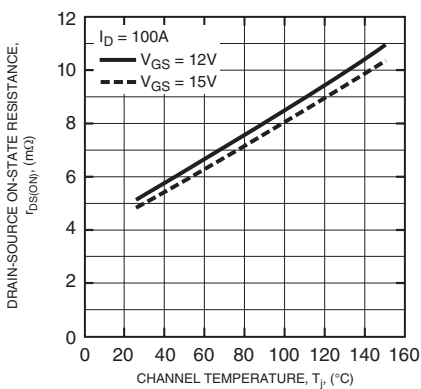
**GATE CHARGE CHARACTERISTICS (TYPICAL)**



**GATE THRESHOLD VOLTAGE VS. TEMPERATURE (TYPICAL)**



**DRAIN-SOURCE ON-STATE RESISTANCE VS. TEMPERATURE (TYPICAL)**



**TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (TYPICAL)**

